

**IN THE SPECIFICATION:**

Please amend the title to read as follows:

**ESD/EOS PROTECTION STRUCTURE FOR INTEGRATED CIRCUIT DEVICES**

Please amend the disclosure as follows:

- On page 3, line 28, please delete the only occurrence of "bipolar";
- On page 4, line 1, please delete the only occurrence of "bipolar";
- On page 5, line 17, please delete the only occurrence of "bipolar";
- On page 5, line 24, please delete the only occurrence of "bipolar";
- On page 6, line 4, please delete the only occurrence of "bipolar";
- On page 6, line 10, please delete the only occurrence of "bipolar";
- On page 7, line 25, please delete the only occurrence of "bipolar";
- On page 9, line 7, please delete the only occurrence of "bipolar";
- On page 11, line 22, please delete the only occurrence of "bipolar";
- On page 11, line 24, please delete the only occurrence of "bipolar";
- On page 12, line 9, please delete the only occurrence of "bipolar";
- On page 13, line 1, please delete ", as shown in FIG. 1,".

**IN THE CLAIMS:**

Please amend claims 1, 3, 4-10, 19, 21, and 28 as follows:

- Sub C1
1. (Twice Amended) A contact for a semiconductor device, comprising:
    - a contact plug extending through a first barrier layer, wherein said contact plug is in electrical communication with an active region on a semiconductor substrate;
    - a contact land disposed atop said contact plug, wherein said contact land [has a larger cross-sectional area] is wider than said contact plug and is substantially planar;
    - an upper contact extending through a second barrier layer, which is disposed over said first barrier layer, to form an electrical [said] contact with said contact land.